Product data sheet

1. General description

PNP low VCEsat transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS305NX-Q

2. Features and benefits

- · Low collector-emitter saturation voltage VCEsat
- High collector current capability IC and ICM
- · High collector current gain (hFE) at high IC
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- · High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- · High-voltage motor control
- · High-voltage power switches (e.g. motors, fans)
- Automotive applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-80	V
I _C	collector current		-	-	-4	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-8	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -4 A; I_B = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	58	83	mΩ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		, , , , , , , , , , , , , , , , , , ,
3	В	base	3 2 1	B—[
			SOT89	sym132

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PBSS305PX-Q	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89				

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS305PX-Q	%5M

[1] % = placeholder for manufacturing site code

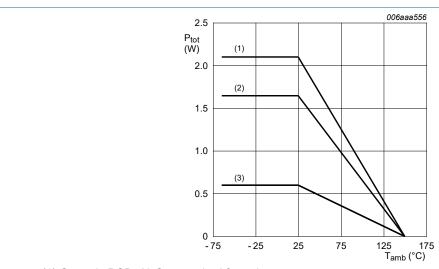
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-80	V
V _{CEO}	collector-emitter voltage	open base		-	-80	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-4	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-8	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.6	W
			[2]	-	1.65	W
			[3]	-	2.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint. [3]



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

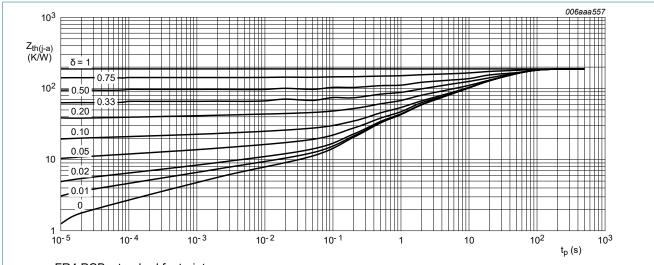
Fig. 1. **Power derating curves**

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from		[1]	-	-	208	K/W
	junction to ambient		[2]	-	-	76	K/W
			[3]	-	-	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

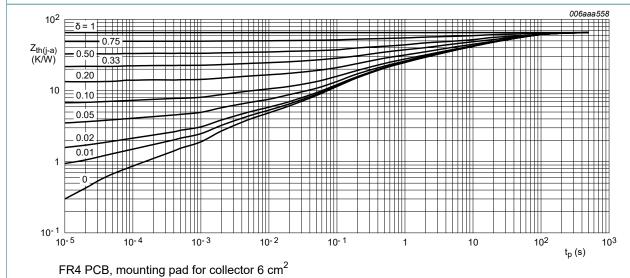
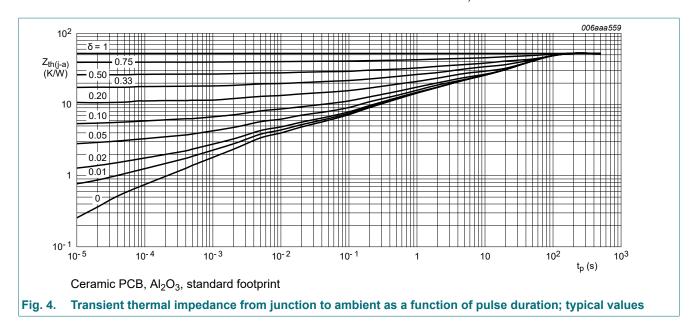


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

80 V, 4.0 A PNP low VCEsat transistor



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{СВО}	collector-base cut-off	V _{CB} = -80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -80 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{ЕВО}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	280	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le 0.02$; T_{amb} = 25 °C	150	240	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	120	190	-	
		V_{CE} = -2 V; I_{C} = -4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	60	100	-	
√ _{CEest} collector-emitter		V_{CE} = -2 V; I_{C} = -5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	45	70	-	
OLSat	collector-emitter saturation voltage	I_C = -0.5 A; I_B = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-36	-50	mV
		I_C = -1 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-70	-100	mV
		I_C = -1 A; I_B = -10 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-180	-250	mV
		I_C = -2 A; I_B = -40 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-200	-280	mV
		I_C = -4 A; I_B = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-230	-330	mV
		I_C = -4 A; I_B = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-170	-240	mV
		I_C = -4.7 A; I_B = -235 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-300	-420	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -40 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	100	140	mΩ
		I_C = -4 A; I_B = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	58	83	mΩ
		I_C = -4 A; I_B = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	43	60	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.81	-0.9	V
		I_C = -4 A; I_B = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.93	-1.05	V
√ _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.78	-0.85	V
d	delay time	V_{CC} = -12.5 V; I_C = -3 A; I_{Bon} = -0.15 A;	-	15	-	ns
r	rise time	I _{Boff} = 0.15 A; T _{amb} = 25 °C	-	85	-	ns
on	turn-on time		-	100	-	ns
·s	storage time		-	185	-	ns
f	fall time		-	100	-	ns
off	turn-off time		-	285	-	ns

80 V, 4.0 A PNP low VCEsat transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	-	100	-	MHz
C _c		V_{CB} = -10 V; I_E = 0 A; i_e = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	65	90	pF

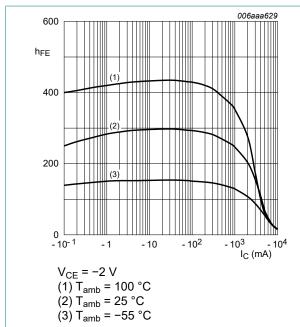


Fig. 5. DC current gain as a function of collector current; typical values

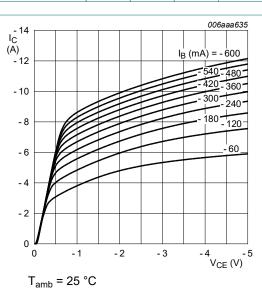


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

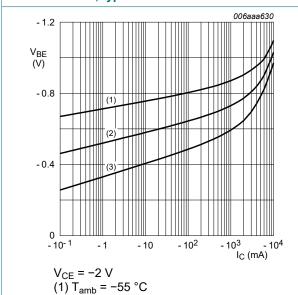
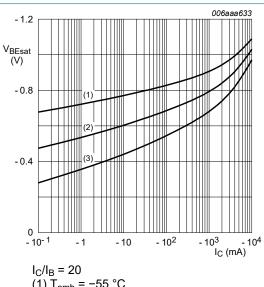


Fig. 7. Base-emitter voltage as a function of collector current; typical values

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C



 $I_C/I_B = 20$ (1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = 100 \,^{\circ}C$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

80 V, 4.0 A PNP low VCEsat transistor

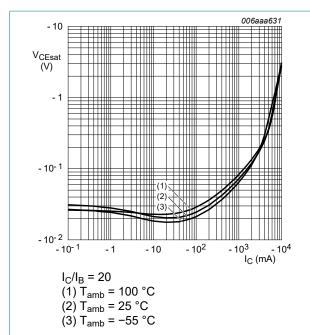


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

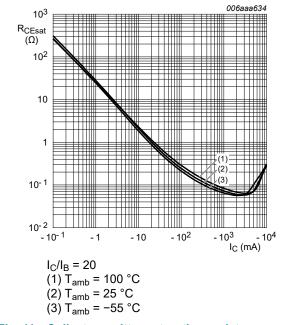


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

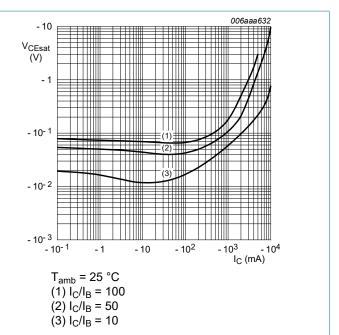


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

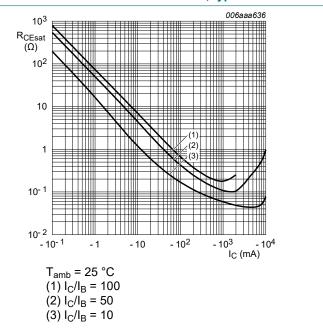
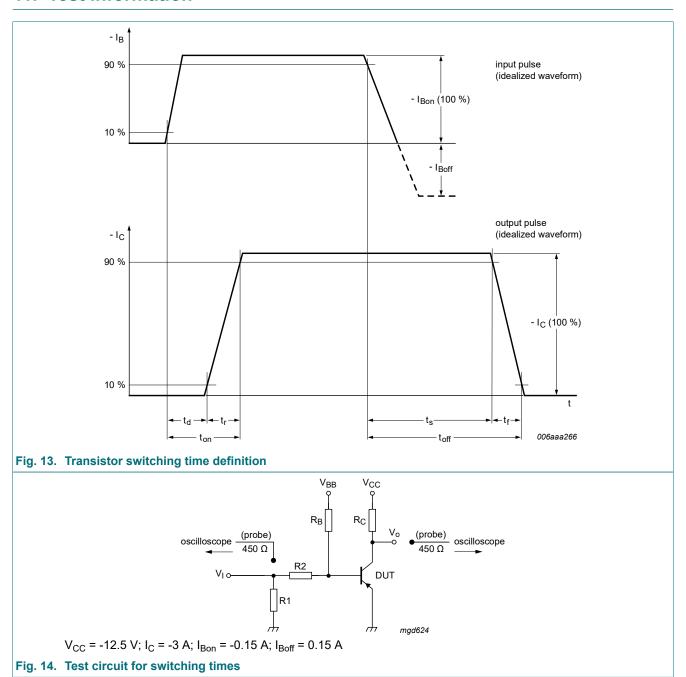


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

80 V, 4.0 A PNP low VCEsat transistor

11. Test information

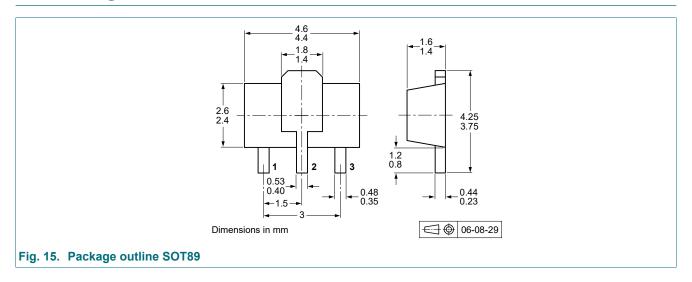


Quality information

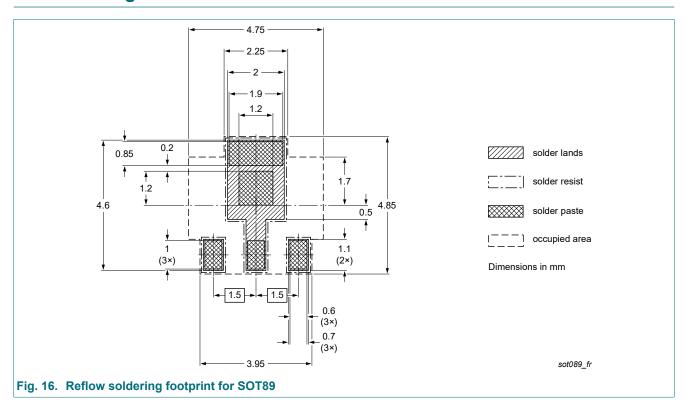
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

80 V, 4.0 A PNP low VCEsat transistor

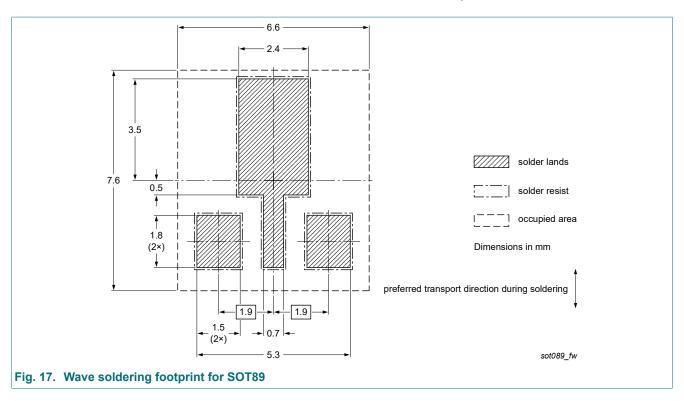
12. Package outline



13. Soldering



80 V, 4.0 A PNP low VCEsat transistor



80 V, 4.0 A PNP low VCEsat transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS305PX-Q v.1	20240214	Product data sheet	-	-

80 V, 4.0 A PNP low VCEsat transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PBSS305PX-Q

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